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TRANSMITTAL FORM (to be used for all correspondence after initial filing)		Application Number		09/886,972
		Filing Date		June 25, 2001
		First Named Inventor		Yoshihisa KATO et al.
		Group Art Unit		2818
		Examiner Name		Ly D. PHAM
Total Number of Pages in This Submission	·	Attorney Docket Number		740819-566
ENCLOSURES (check all that apply)				
Fee Transmittal Form Fee Attached Amendment / Reply After Final Affidavits/declaration(s) Extension of Time Request Express Abandonment Request Information Disclosure Statement Certified Copy of Priority Document(s) Response to Missing Parts/ Incomplete Application Response to Missing Parts under 37 CFR 1.52 or 1.53	Drawing Declarate Licensin Petition Petition Applicate Power of Change Termina Request	tion and Power of Attorney ng-related Papers to Convert to a Provisional tion f Attorney, Revocation of Correspondence Address I Disclaimer for Refund mber of CD(s)	ayme	After Allowance Communication to Group Appeal Communication to Board of Appeals and Interferences Appeal Communication to Group (Appeal Notice, Brief, Reply Brief) Proprietary Information Status Letter Application Data Sheet Other Enclosure(s) (please Alentify below):
SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT				
Firm Donald R. Studebaker, Reg. No. 32,815				

Firm or Individual name Donald R. Studebaker, Reg. No. 32,815 Nixon Peabody LLP 8180 Greensboro Drive Suite 800 McLean, VA 22102 Signature Date March 14, 2003

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Docket No. 740819-566

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

)

Group Art Unit: 2818

Date: March 14, 2003

Patent Application of:

Yoshihisa KATO et al.

Serial No. 09/886,972) Examiner: Ly D. PHAM

Filed: June 25, 2001

For: SEMICONDUCTOR MEMORY AND

METHOD FOR DRIVING THE SAME

7/ Alspone G. Storly 3-18-03

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REQUEST FOR RECONSIDERATION

Commissioner for Patents Washington, D.C. 20231

Sir:

In response to the Office Action mailed December 16, 2002, please consider Applicants' following remarks in connection with the above-identified application.

REMARKS

The Office Action December 16, 2002 was received and reviewed. Applicants would like to thank the Examiner for the consideration given to the above-identified application.

Claims 1-4 are pending in the present application, of which claims 3 and 4 have been withdrawn from consideration in a response to an election requirement dated October 8, 2002.

Referring now to the detailed Office Action, claim 1 stand rejected under 35 U.S.C. §102(e) as anticipated by Taira (U.S. Patent No. 6,049,477), and claim 2 stand rejected under 35 U.S.C. §103(a) as unpatentable over Taira in view of Ishiwara (U.S. Patent No. 6,362,500). Both of these rejections have been previously applied for the same reasons as stated in the Office Action of June 14, 2002. Applicants respectfully traverse these rejections at least for the reasons provided below.

One of the main features of the invention in the claim 1 or 2 resides in the magnitude of the data read voltage applied between the drain and the source of the FET (field effect transistor)

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